NPN Epitaxial Planar Silicon Transistor



2SC4306

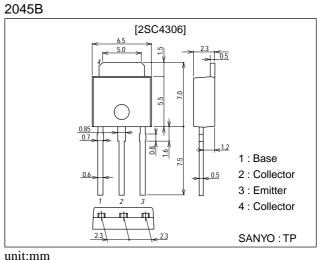
# **High-Current Switching Applications**

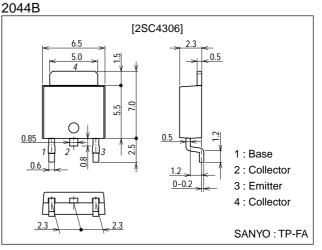
## Features

- · Adoption of FBET, MBIT processes.
- $\cdot$  Low saturation voltage.
- · Fast switching speed.
- · Large current capacity.
- Small and slim package making it easy to make 2SC4306-used set smaller.

## Package Dimensions

unit:mm





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## **Specifications**

## Absolute Maximum Ratings at $Ta = 25^{\circ}C$

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	VCBO		30	V
Collector-to-Emitter Voltage	VCEO		20	V
Emitter-to-Base Voltage	VEBO		5	V
Collector Current	IC		8	А
Collector Current (Pulse)	ICP		12	А
Base Current	Ι <sub>Β</sub>		1.5	А
Collector Dissipation	PC		1	W
		Tc=25°C	15	W
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		-55 to +150	°C

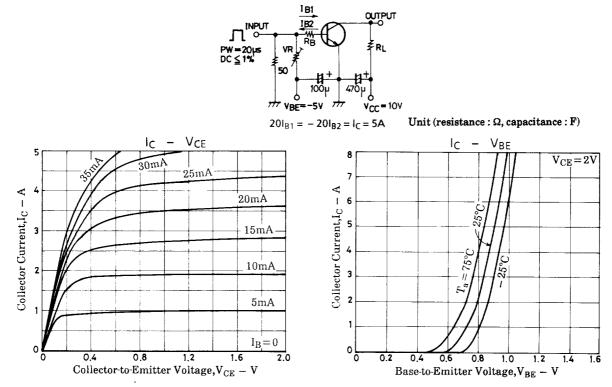
## Electrical Characteristics at Ta = 25°C

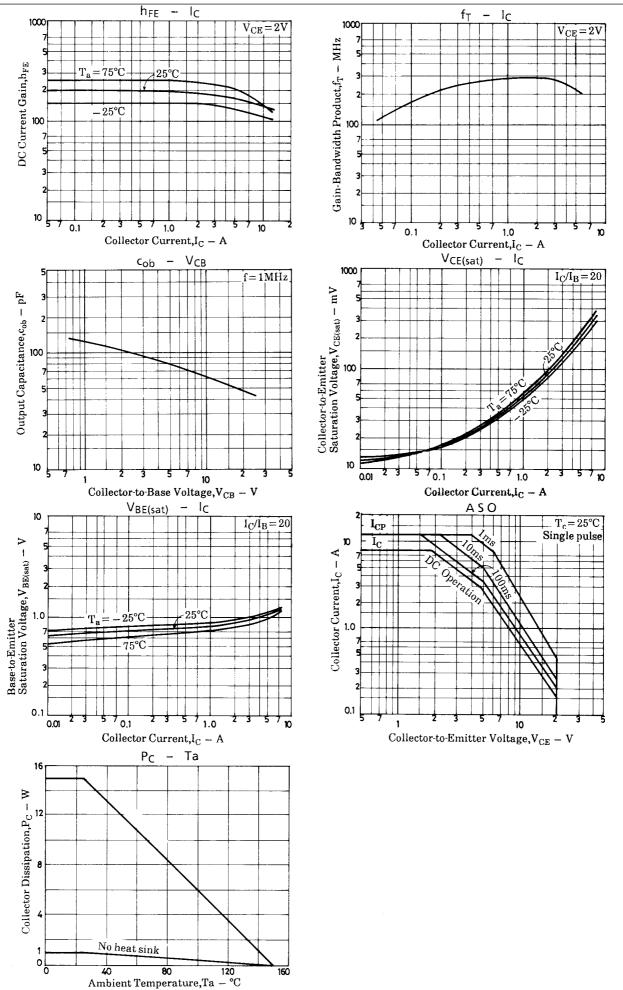
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Unit
Collector Cutoff Current	ICBO	V <sub>CB</sub> =20V, I <sub>E</sub> =0			1	μΑ
Emitter Cutoff Current	IEBO	$V_{EB}=4V, I_{C}=0$			1	μΑ
DC Current Gain	h <sub>FE</sub> 1	V <sub>CE</sub> =2V, I <sub>C</sub> =500mA	100*		400*	
	h <sub>FE</sub> 2	V <sub>CE</sub> =2V, I <sub>C</sub> =6A	70			
Gain-Bandwidth Product	fT	V <sub>CE</sub> =2V, I <sub>C</sub> =500mA		250		MHz
Output Capacitance	C <sub>ob</sub>	V <sub>CB</sub> =10V, f=1MHz		60		pF
Collector-to-Emitter Saturation Voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =5A, I <sub>B</sub> =250mA		220	400	mV
Base-to-Emitter Saturation Voltage	V <sub>BE(sat)</sub>	IC=5A, IB=250mA		1	1.3	V
Collector-to-Base Breakdown Voltage	V <sub>(BR)</sub> CBO	I <sub>C</sub> =10μA, I <sub>E</sub> =0	30			V
Collector-to-Emitter Breakdown Voltage	V(BR)CEO	I <sub>C</sub> =1mA, R <sub>BE</sub> =∞	20			V
Emitter-to-Base Breakdown Voltage	V(BR)EBO	I <sub>E</sub> =10μA, I <sub>C</sub> =0	5			V
Turn-ON Time	ton	See specified test circuit.		30	300	ns
Storage Time	tstg	See specified test circuit.		250	1000	ns
Fall Time	t <sub>f</sub>	See specified test circuit.		15	150	ns

 $\ast$  : The 2SC4306 is classified by 500mA  $h_{FE}$  as follows :

100 R 200 140 S 280 200 T 400

### **Switching Time Test Circuit**





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